

Clean copy, pursuant to 37 C.F.R. § 1.121(b)(1)(ii), of the paragraph amended at page 2 of  
the specification:

*PF*  
This is a divisional application of US Patent Application Serial No. 08/846,671, filed on  
April 30, 1997, *Pat. 6,849,557*, titled "UNDOPED SILICON DIOXIDE AS ETCH STOP FOR SELECTIVE ETCH  
OF DOPED SILICON DIOXIDE", which is incorporated herein by reference.

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